

5 - 44GHz Detector

GaAs Monolithic Microwave IC

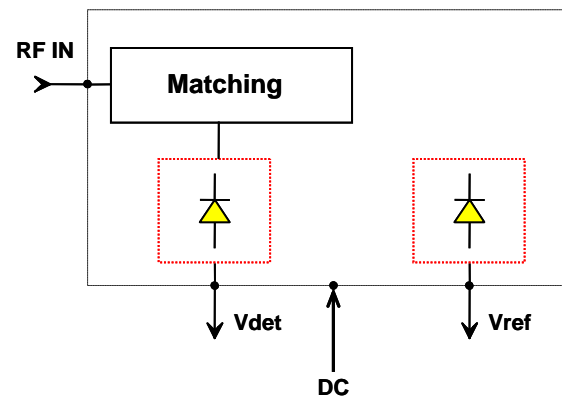
Description

The CHE1270a99F is a detector that integrates a matched detection diode (V_{det}). A reference diode is also available to be used in differential mode (V_{ref}).

It is designed for a wide range of applications where an accurate transmitted power control is required, typically commercial communication systems.

The circuit is manufactured with a Schottky diode MMIC process, 1 μ m gate length, via holes through the substrate and air bridges.

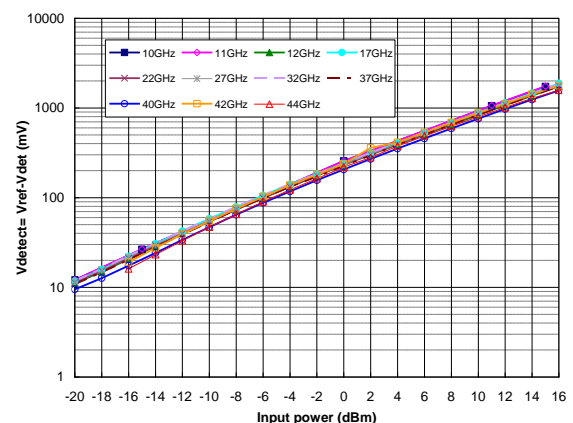
It is available in chip form.



Main Features

- Wide frequency range 5-44GHz
- 30dB dynamic range
- ESD protected
- Chip size: 1.41 x 0.89 x 0.1mm

Transmitted power detection (mV)



Main Characteristics

Tamb.= +25°C

| Symbol | Parameter | Min | Typ | Max | Unit |
|--------|-----------------|-----|-----|-----|------|
| Freq | Frequency range | 5 | | 44 | GHz |
| Dr | Dynamic range | 30 | | | dB |
| RL | Return Loss | | -10 | | dB |

Main Characteristics

Tamb.= +25°C, Vdc = +4.5V

| Symbol | Parameter | Min | Typ | Max | Unit |
|---------|---|-----|-----|------|------|
| Freq | Frequency range | 5 | | 44 | GHz |
| Dr | Dynamic range (for Input Power detection) | 30 | | | dB |
| IPd | Input Power detection | -15 | | 15 | dBm |
| Vdetect | Voltage detection Vref – Vdet from IPd_min to IPd_max | 5 | | 2200 | mV |
| RL | Return Loss (5 – 10GHz) | | -4 | -3 | dB |
| | Return Loss (10 – 12GHz) | | -7 | -5 | dB |
| | Return Loss (12 – 14.5GHz) | | -8 | -6 | dB |
| | Return Loss (14.5 – 42GHz) | | -10 | -8 | dB |
| | Return Loss (42 – 44GHz) | | -7 | -5 | dB |
| Vdc | Bias voltage | | 4.5 | | V |
| Idc | Bias current | 50 | 70 | 90 | μA |

These values are representative of on-wafer measurements that are made without bonding wires at the RF ports but with 27kΩ resistor in parallel on pads Vdet and Vref.

Absolute Maximum Ratings ⁽¹⁾T_{amb.} = +25°C

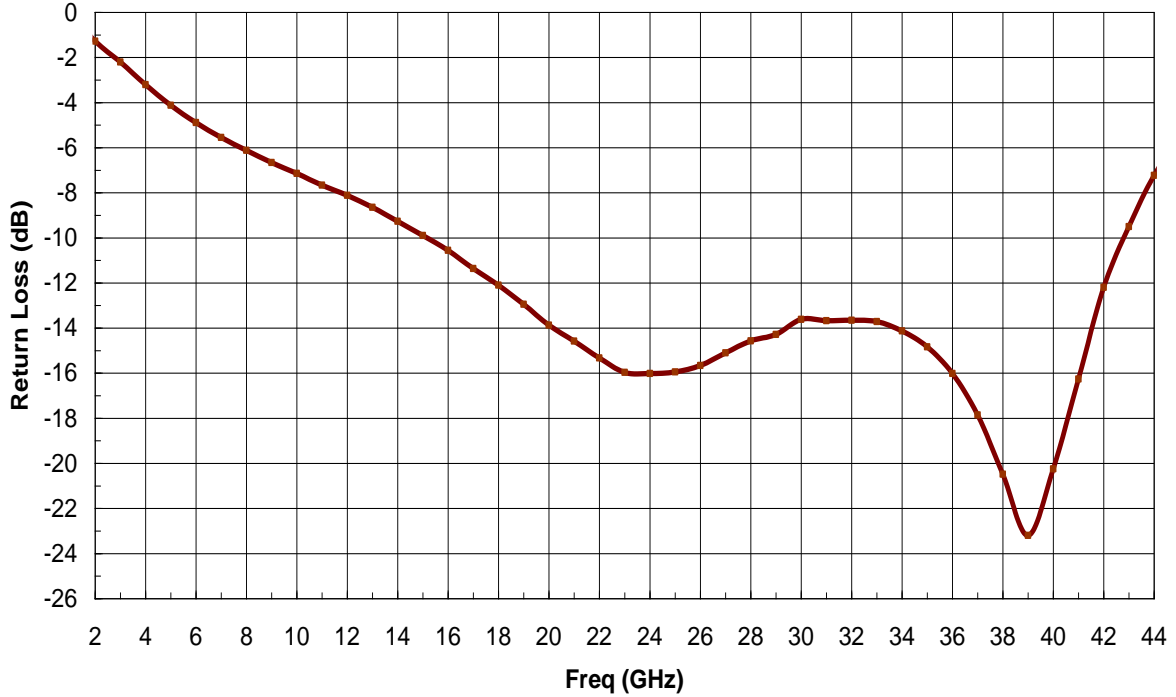
| Symbol | Parameter | Values | Unit |
|--------------------|-------------------------------|-------------|------|
| V _{dc} | Drain bias voltage | 6V | V |
| IP _{dmax} | Maximum Input Power detection | +18 | dBm |
| T _a | Operating temperature range | -40 to +95 | °C |
| T _{stg} | Storage temperature range | -55 to +150 | °C |

⁽¹⁾ Operation of this device above any one of these parameters may cause permanent damage.

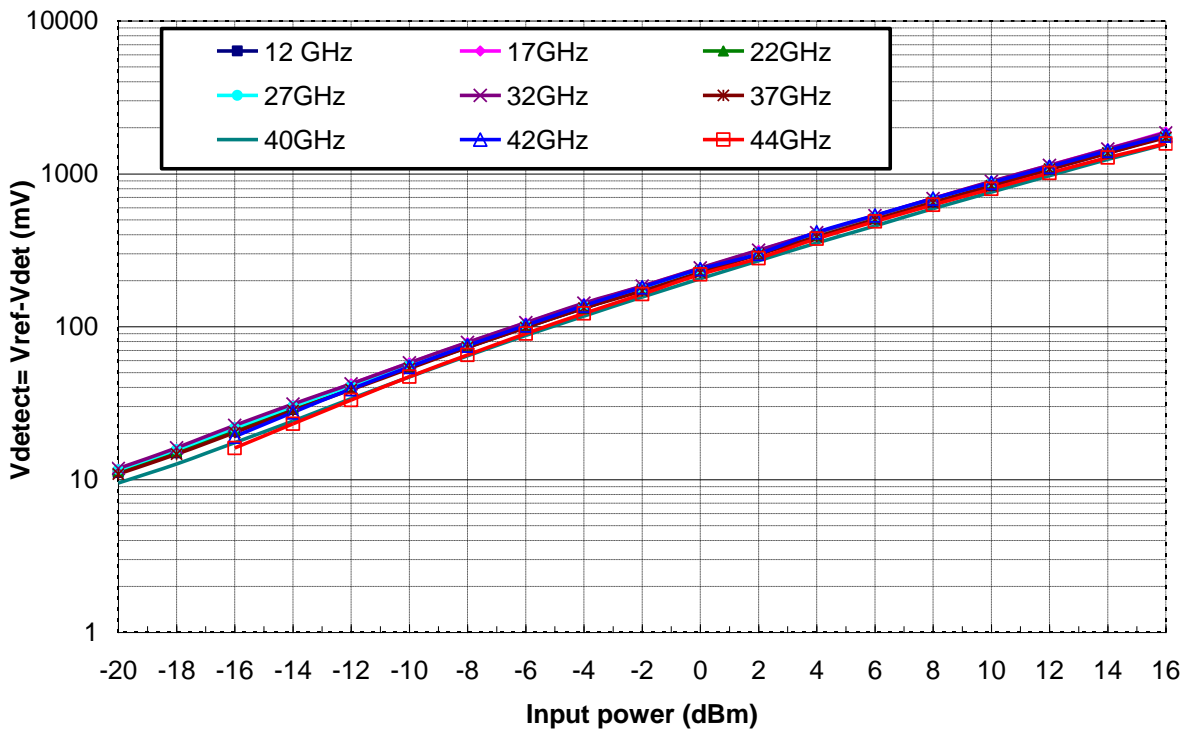
Typical on wafer Measurements

Tamb.= +25°C, Vdc = +4.5V

Return Loss versus frequency

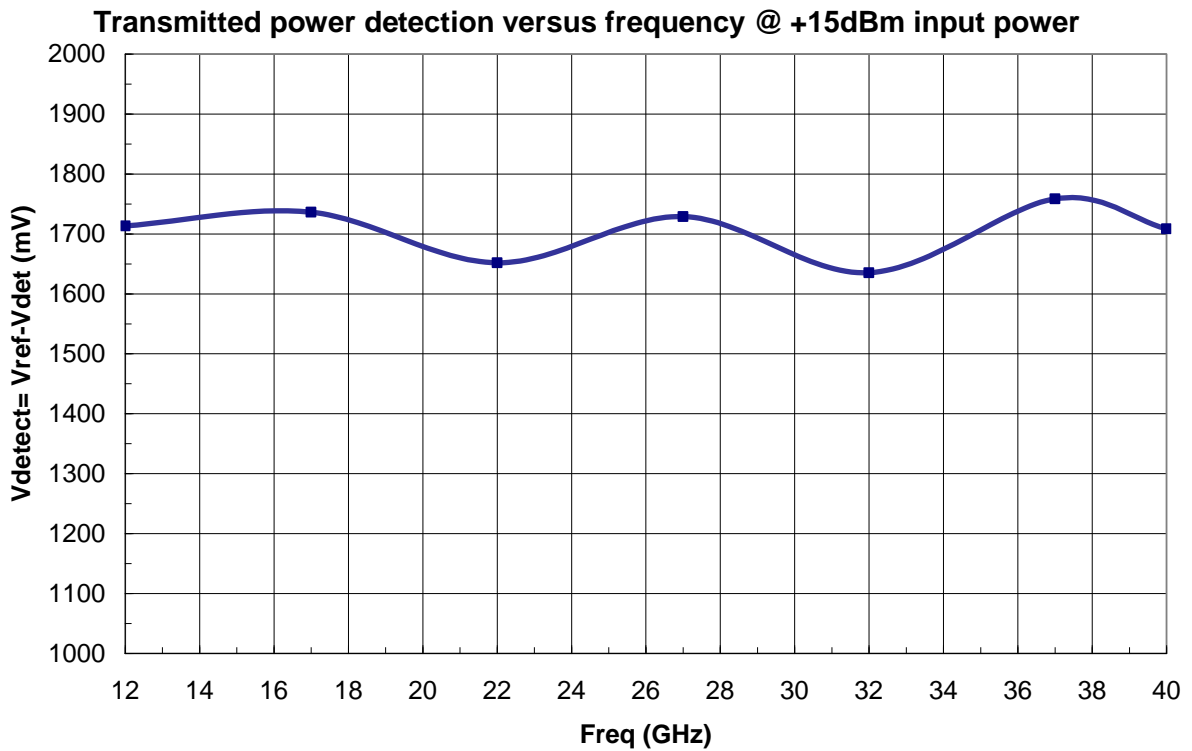
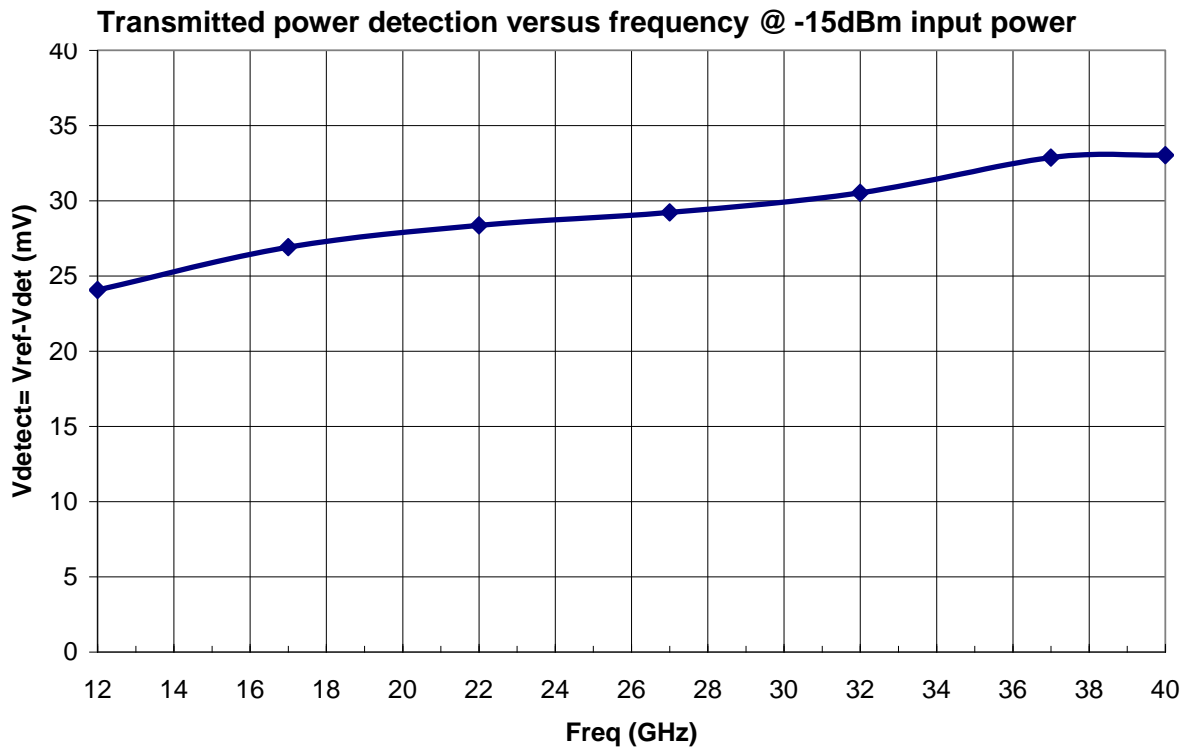


Transmitted power detection

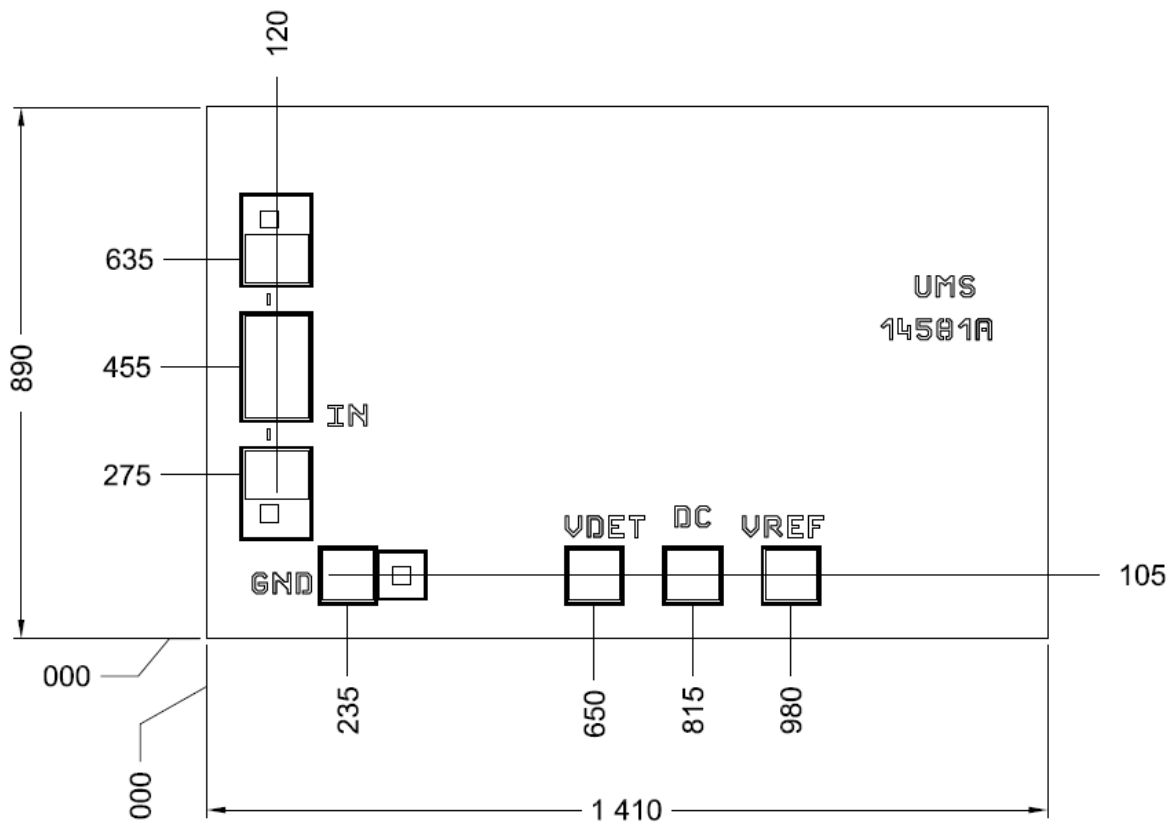


Typical on wafer Measurements

Tamb.= +25°C, Vdc = +4.5V



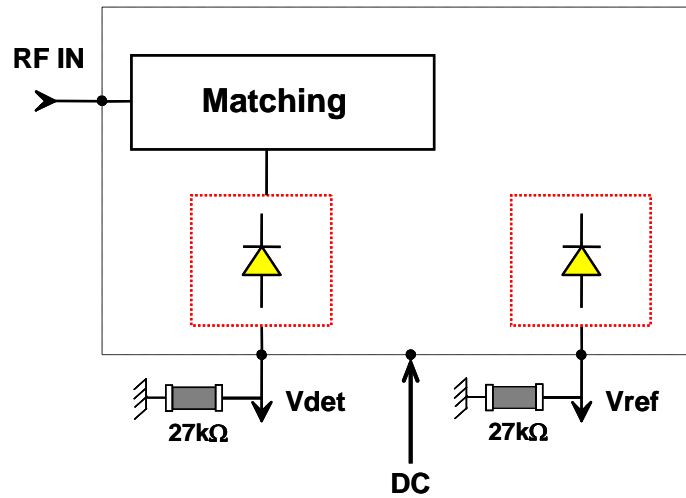
Mechanical data



Chip thickness: 100µm
 Chip size: 1.41 x 0.89 x 0.1mm ±35µm
 DC Pads Size: 100/100 µm
 All dimensions are in micrometers

Note: Supply feed might be capacitively bypassed. 25µm diameter gold wire is to be preferred.

Notes



Recommended external resistors assembly

27k Ω resistors in parallel with Vdet and Vref pads are recommended to provide the best behaviour in the whole operating temperature range.

As the voltage detection is the difference between Vref and Vdet, the external resistor value should be identical on these two ports.

For information, a variation of 3% leads around 1mV variation of detected voltage.

Due to ESD protection circuits on RF input, an external capacitance might be requested to isolate the product from external voltage that could be present on the RF access. ESD protections are also implemented on Vdet and Vref accesses.

Recommended ESD management

Refer to the application note AN0020 available at <https://www.ums-rf.com> for ESD sensitivity and handling recommendations for the UMS products.

Recommended environmental management

UMS products are compliant with the regulation in particular with the directives RoHS N°2011/65 and REACH N°1907/2006. More environmental data are available in the application note AN0019 also available at <https://www.ums-rf.com>.

Ordering Information

Chip form:

CHE1270a99F/00

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